

Supplementary Materials

Thermoelectric transport properties of BaFe₂Fe₁₆O₂₇ hexaferrites

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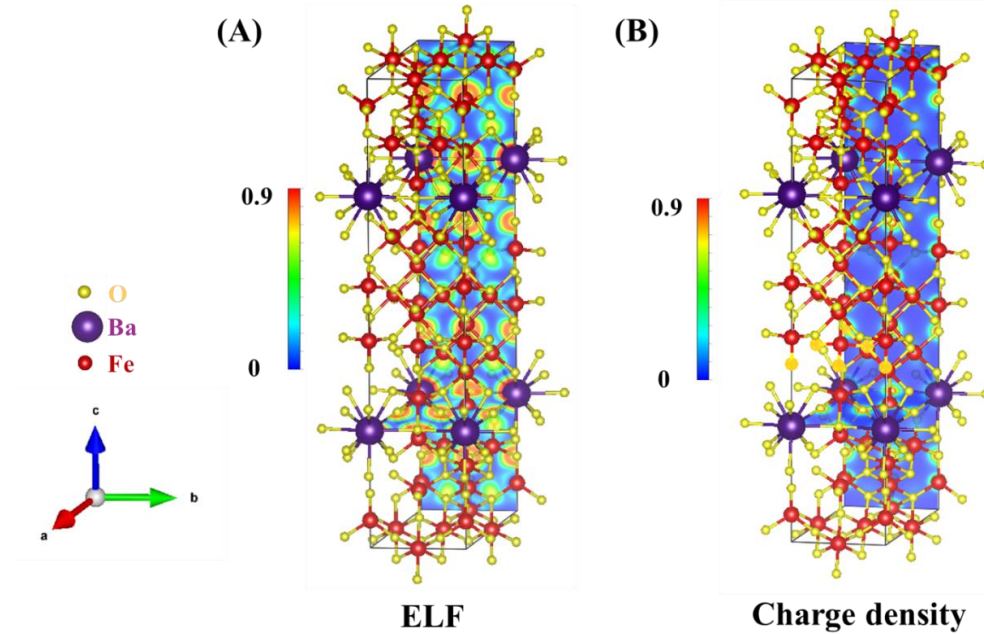


Figure S1. Calculated electron localization function (ELF) and charge transfer of Fe₂W.

We fitted the C_p data with one Debye model and two Einstein models based on ^[1,2]

$$\frac{C_p}{T} = \varphi + \beta T^2 + A \Theta_{E1}^2 (T^2)^{-3/2} \cdot \frac{e^{\Theta_{E1}/T}}{(e^{\Theta_{E1}/T} - 1)^2} + B \Theta_{E2}^2 \cdot \frac{e^{\Theta_{E2}/T}}{(e^{\Theta_{E2}/T} - 1)^2} \quad (1)$$

where φ , β are the electronic and Debye lattice contribution, respectively. Θ_{Ei} ($i = 1, 2$) is the

Einstein temperature of the two local vibrational modes, and A and B are the constants. In addition, Debye temperature can be estimated according to ^[2]

$$\Theta_D = (12\pi^4 pR/5\beta)^{1/3} \quad (2)$$

where R is the gas constant and p is the number of atoms in each molecule.

Table S1. Parameters obtained by fitting the low-temperature specific heat capacity of BaFe₂Fe₁₆O₂₇ using Debye-Einstein model.

Parameter (Unit)	Value
φ (10^{-3} J/mol K ⁻²)	44.5
β (10^{-4} J/mol K ⁻²)	6.5
Θ_{E1} (K)	47.7
Θ_{E2} (K)	127
A	10.5
B	70.0
θ_D (K)	516

Temperature-dependent lattice thermal conductivity could be modeled by using the Debye approximation

$$\kappa_L = \frac{k_B}{2\pi^2 v} \left(\frac{k_B T}{\hbar}\right)^3 \int_0^{\theta_D/T} \frac{x^4 e^x}{\tau_C^{-1}(e^x - 1)^2} dx \quad (3)$$

where the dimensionless quantity can be expressed as

$$x = \hbar\omega/k_B T \quad (4)$$

where k_B is the boltzmann constant, ω is the phonon frequency, \hbar is the reduced Planck constant, θ_D is the Debye temperature, v is the sound velocity, and τ_C is the phonon-scattering relaxation time. The phonon-scattering relaxation time τ_C can be expressed by

$$\tau_C^{-1} = \frac{v}{L} + A\omega^4 + B\omega^2 T \exp\left(-\frac{\theta_D}{3T}\right) \quad (5)$$

where L is the grain size and the coefficients A, B are the fitting parameters which related to the point defect scattering and Umklapp scattering, respectively. The terms on the right side of Equation 10 represent the influence of grain boundary, point defect, and phonon-phonon umklapp, respectively. θ_D and v for Fe₂W-based ceramics are calculated by DFT calculation and values are 517 K and 3667 m/s (listed in Table 1), respectively.

$$A = \frac{\Omega_0}{4\pi v^3} \Gamma_{\text{exp}} \quad (6)$$

$$\Gamma_{\text{mass}}(U_u V_v W_w) = \frac{u \left(\frac{M_u}{M_m}\right)^2 \Gamma(U) + v \left(\frac{M_v}{M_m}\right)^2 \Gamma(V) + w \left(\frac{M_w}{M_m}\right)^2 \Gamma(W)}{u+v+w} \quad (7)$$

$$\Gamma = \Phi(1 - \Phi) \left(\frac{\Delta M}{M_{av}}\right)^2 \quad (8)$$

$$\Delta M = M_i - M_h \quad (9)$$

$$M_{av} = \Phi M_i + (1 - \Phi) M_h \quad (10)$$

$$\Gamma_{\text{strain}} = \Gamma_{\text{exp}} - \Gamma_{\text{mass}} \quad (11)$$

where Ω_0 is the volume of the primitive cell and Γ_{exp} is an experimental disorder scattering parameter. M_i and M_h are the masses of the impurity and host atoms, respectively.

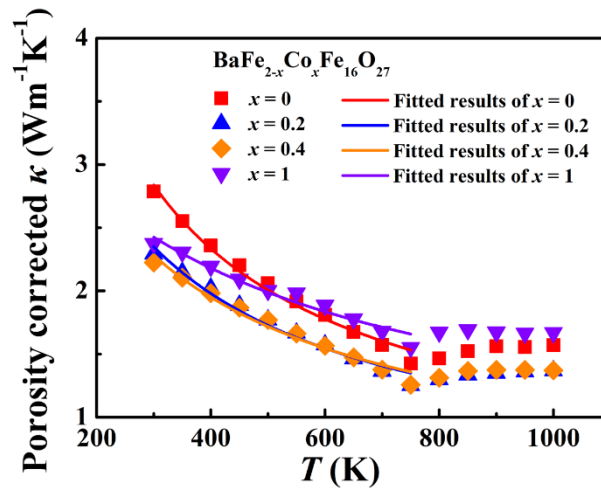


Figure S2. Porosity corrected thermal conductivities as functions of content of temperature for all $\text{BaFe}_{2-x}\text{Co}_x\text{Fe}_{16}\text{O}_{27}$ ($x = 0, 0.2, 0.4, 1.0$) ceramics ranged from 300 K to 750 K.

REFERENCES

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2. Jiang B, Qiu P, Eikeland E, Chen H, Song Q, et al. Cu_8GeSe_6 -based thermoelectric materials with an argyrodite structure. *J Mater Chem C* 2017;5:943-52. DOI: 10.1039/C6TC05068A.